

LN78

GaAlAs Infrared Light Emitting Diode

For optical control systems

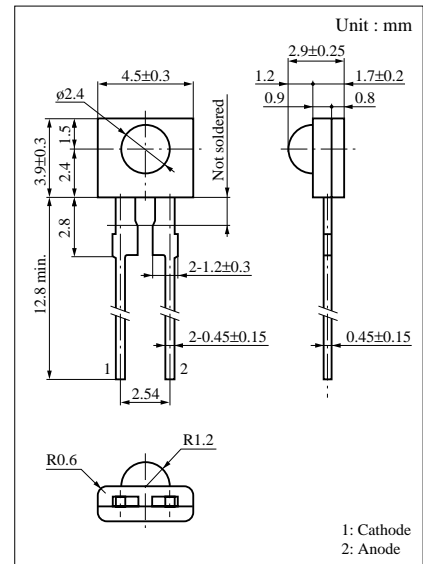
■ Features

- High-power output, high-efficiency : $P_O = 10 \text{ mW}$ (typ.)
- High-speed modulation capability : $f_C = 12 \text{ MHz}$

■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Power dissipation	P_D	180	mW
Forward current (DC)	I_F	100	mA
Pulse forward current	I_{FP}^*	1	A
Reverse voltage (DC)	V_R	3	V
Operating ambient temperature	T_{opr}	-25 to +85	°C
Storage temperature	T_{stg}	-30 to +100	°C

* f = 100 Hz, Duty cycle = 0.1 %



■ Electro-Optical Characteristics (Ta = 25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Radiant power	P_O	$I_F = 50 \text{ mA}$	6	10		mW
Peak emission wavelength	λ_P	$I_F = 50 \text{ mA}$		880		nm
Spectral half band width	$\Delta\lambda$	$I_F = 50 \text{ mA}$		50		nm
Forward voltage (DC)	V_F	$I_F = 100 \text{ mA}$		1.5	1.8	V
Reverse current (DC)	I_R	$V_R = 3 \text{ V}$			10	μA
Capacitance between pins	C_t	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$		50		pF
Half-power angle	θ	The angle in which radiant intensity is 50%		40		deg.
Cutoff frequency	f_C^*	$I_{FP} = 50 \text{ mA} + 10 \text{ mA}_{p-p}$		12		MHz

* Frequency when modulation optical power decreases by 3dB from 1MHz. $\left(10 \log \frac{P_O(f_C \text{ MHz})}{P_O(1 \text{ MHz})} = -3\right)$

